



AIDA²⁰

Gain Stabilization of SiPMs and Afterpulsing

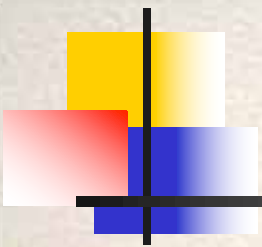
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Photodetector Workshop Tokyo November 28, 2018

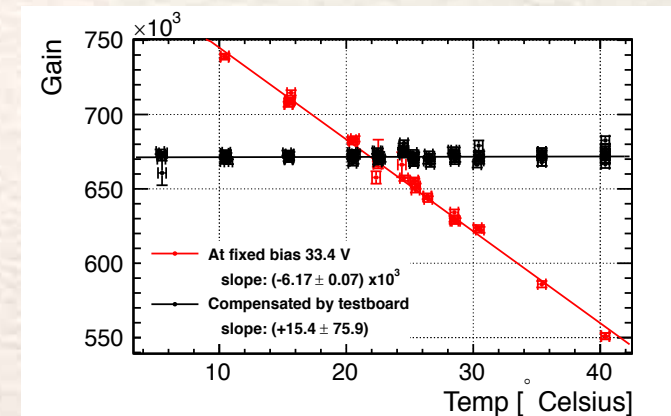


Outline

- Introduction
- Measurement methodology
- Determination of dV_b/dT
- Gain stabilization of Hamamatsu MPPCs
- Gain stabilization of KETEK SiPMs
- Gain stabilization of CPTA SiPMs
- Studies of afterpulsing
- Conclusions and outlook

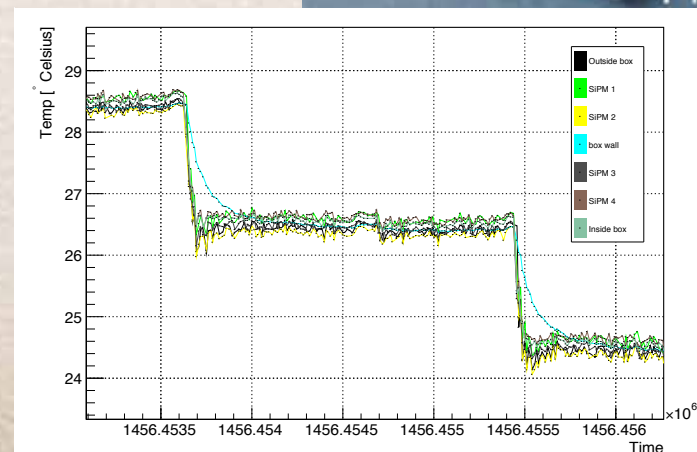
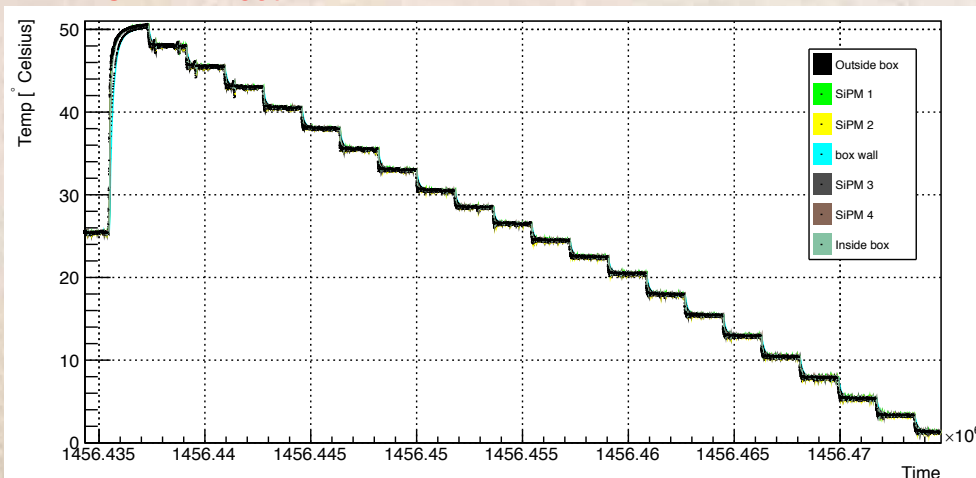
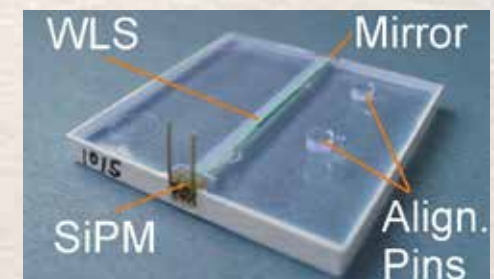
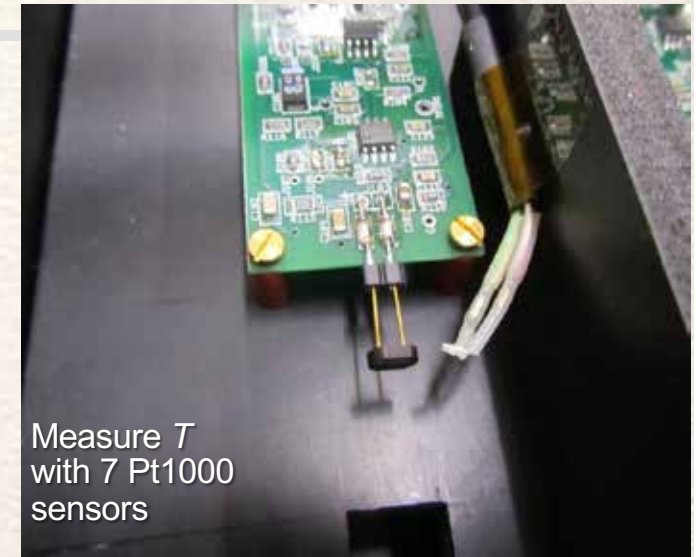
Introduction

- The gain of SiPMs increases with bias voltage V_b and decreases with temperature T
- To operate SiPMs at stable gain, V_b can be readjusted to compensate for T changes
- This requires the knowledge of dV_b/dT , which is obtained from measurements of G vs V_b for different T to extract dG/dV and dG/dT and in turn dV/dT
- Gain stability is important for large detector arrays such as an analog hadron calorimeter for ILC detector
- We tested this procedure in a climate chamber at CERN
 - 1.) For each of 30 SiPMs, we measured G vs V_b for different T to extract dV_b/dT from measurements of dG/dV_b and dG/dT
 - 2.) We performed gain stabilization of **30** SiPMs from Hamamatsu, KETEK & CPTA stabilizing 4 SiPMs simultaneously with one dV_b/dT compensation value
 - ➔ perform automatic compensation with adaptive power supply
- Goal: **define stable gain**
if $\Delta G/G < \pm 0.5\%$ in **20°-30°C** range



Temperature Measurements

- We shine blue LED light of similar intensity via optical fibers on each SiPM
- At a rate of 10kHz, the light is pulsed using sinusoidal pulse above a fixed threshold; signal is 3.4 ns wide
- Each signal of the 4 SiPMs is recorded with a 12 bit digital scope after amplification by a 2-stage preamp
- Hamamatsu & KETEK SiPMs are illuminated directly
- CPTA sensors are glued to a WLS fiber placed in a groove in a scintillator tile
→ light has to pass through the tile and WLS fiber
- Vary T from 48°-2°C (20°-30°C) in 2.5°C (2°C) steps
 - $T_{\text{SiPM}} = T_{\text{set}} \pm 0.5^\circ\text{C}$ (ramp up/down); accuracy $\sim \pm 0.2^\circ\text{C}$



Study of Hamamatsu MPPCs with Trenches

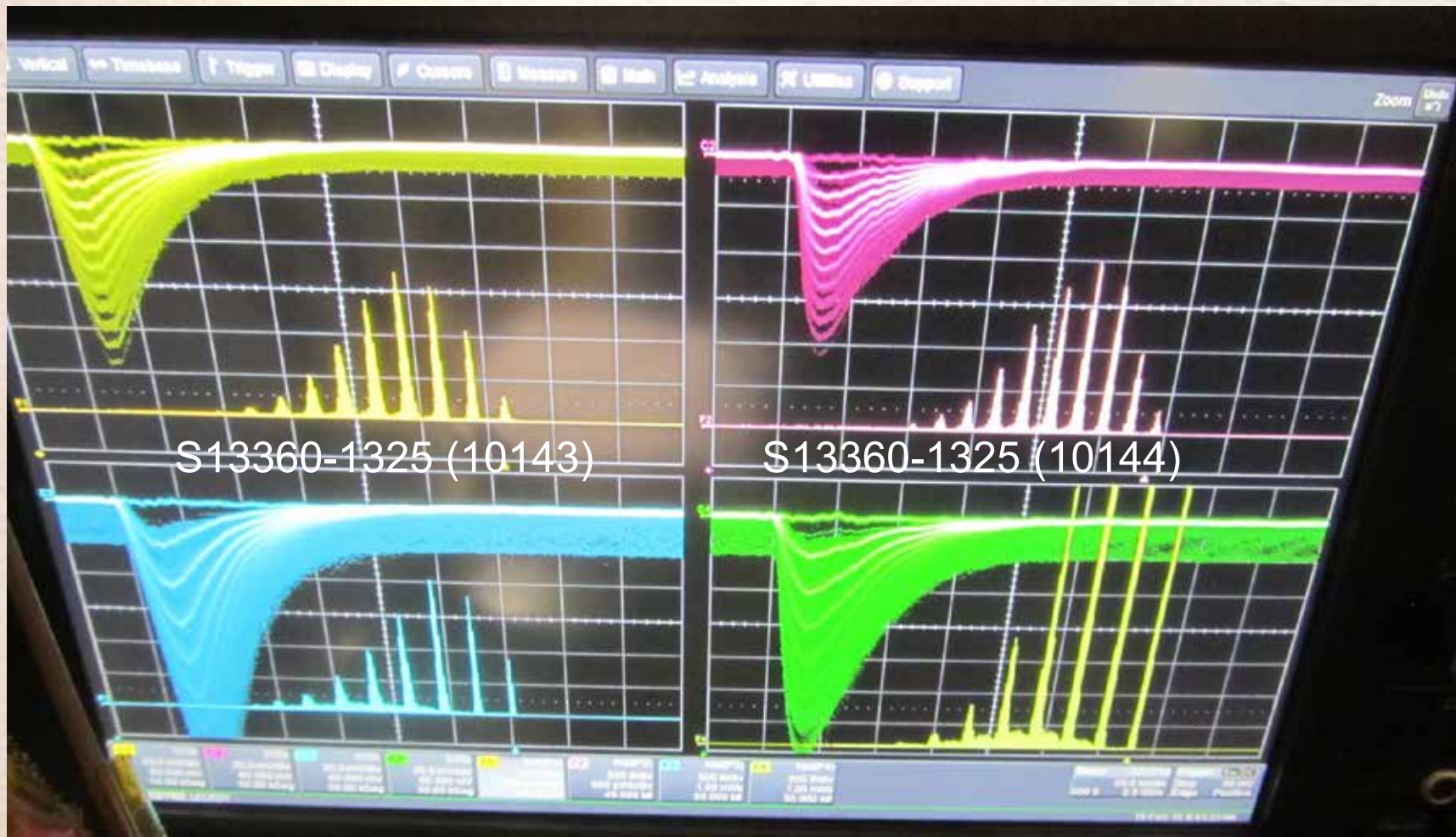
- Waveform and photoelectron spectra of 4 S13360 MPPCs (trenches)

S13360-3025 (10103)

S13360-3025 (10104)

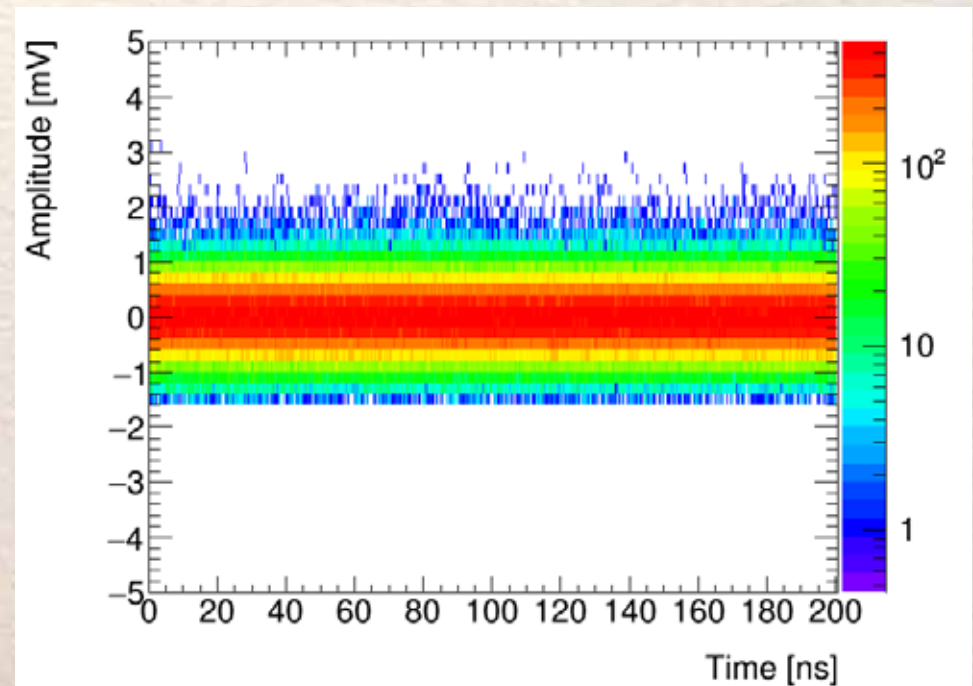
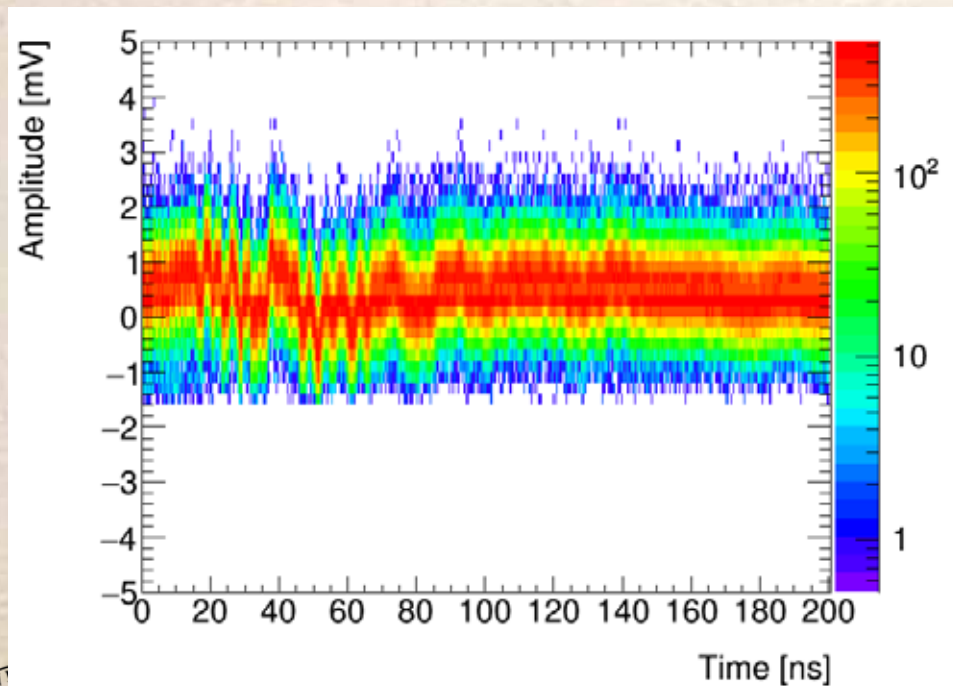
S13360-1325 (10143)

S13360-1325 (10144)



Removal of Parasitic Noise Signal

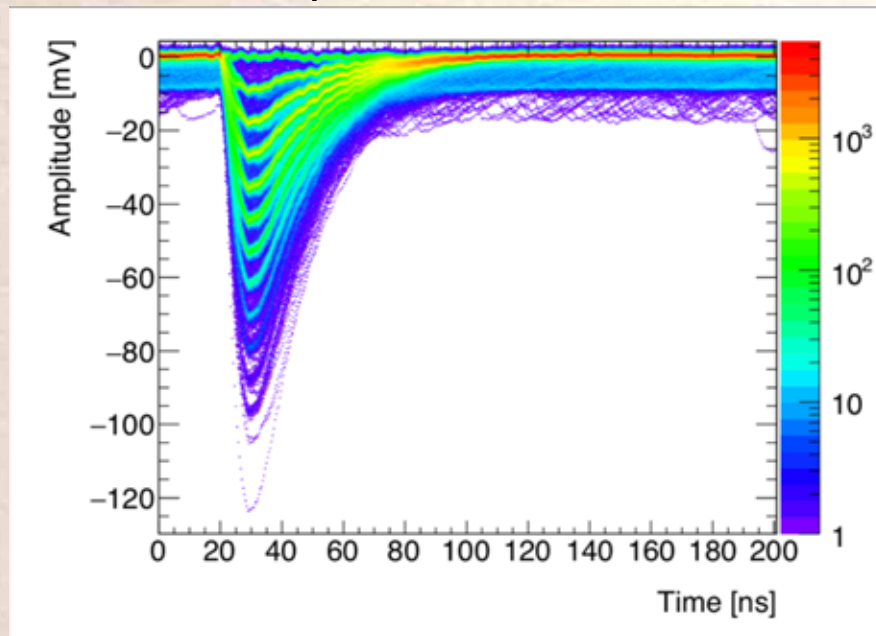
- We remove a parasitic noise signal caused by a defective light pulser cable
- First, we sample 21 points before the signal waveform starts (8.4 ns)
- We fit the distribution with a Gaussian function and define a threshold by $\mu - 3\sigma$
- We select all pedestal distributions that lie above the threshold
- We determine the average and subtract it from all waveforms



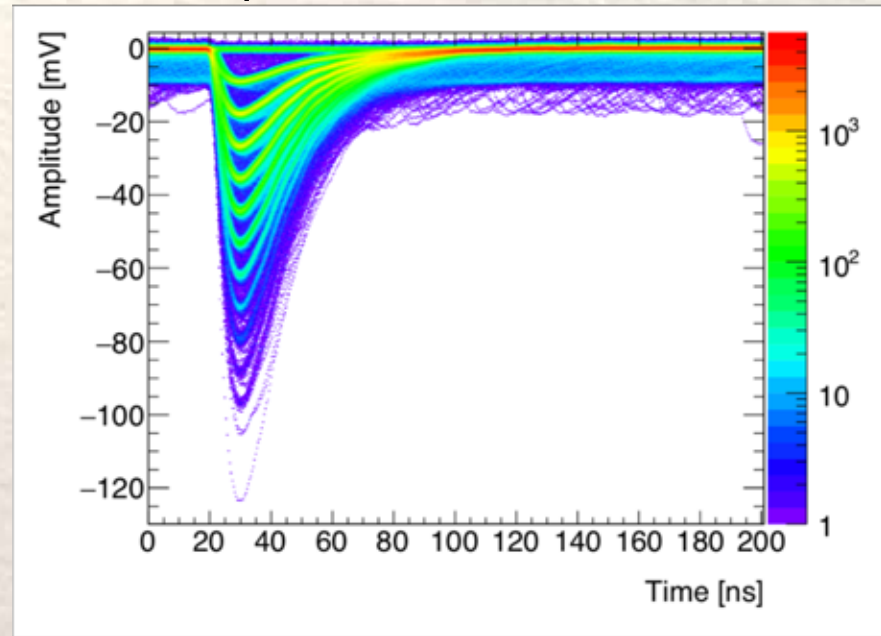
Removal of Parasitic Noise Signal

- Removing the parasitic noise signal improves the shape of the waveforms
- This, in turn, improves the determination of the peak positions

Before parasitic noise removal



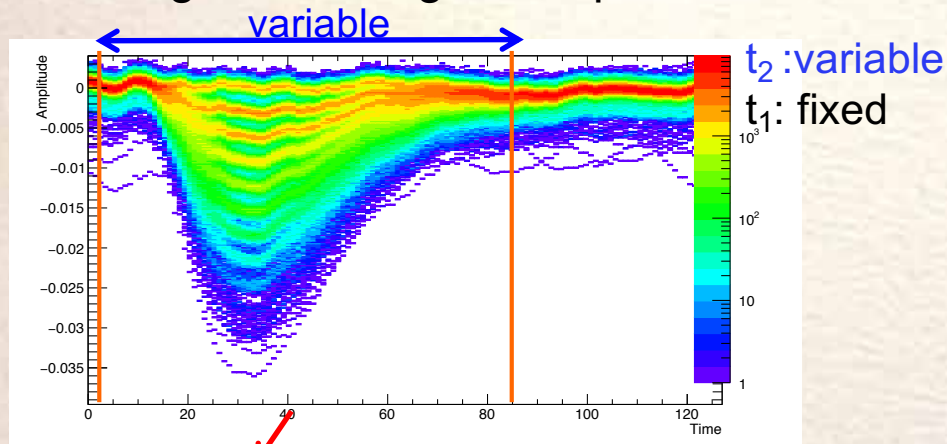
After parasitic noise removal



- We then extract the photoelectron spectra using 2 methods
 - Integrate waveform over variable time window (fixed start, variable end)
 - Determine minimum of the waveform

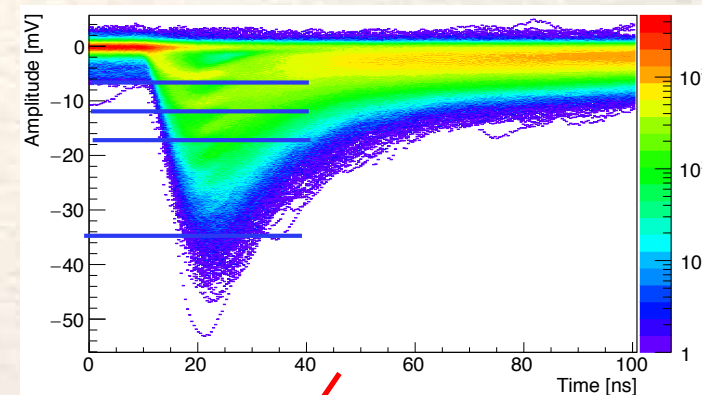
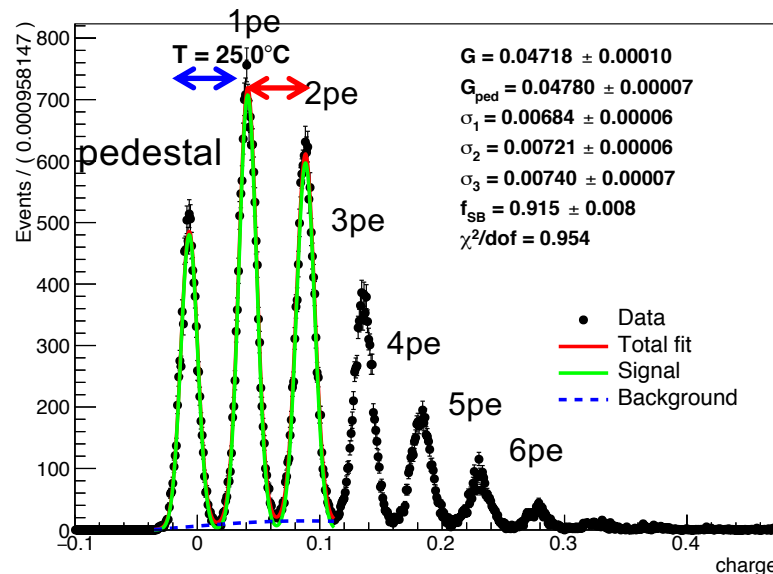
2 Methods to Extract Photoelectron Spectra

- We take 50000 waveforms at each V_b and T point and store them for offline analysis
- Integrate each waveform over t_2 - t_1 window
→ total charge, see integer # of pe
- Determine minimum of waveform amplitude
→ A_{peak} , typically see integer # of pe



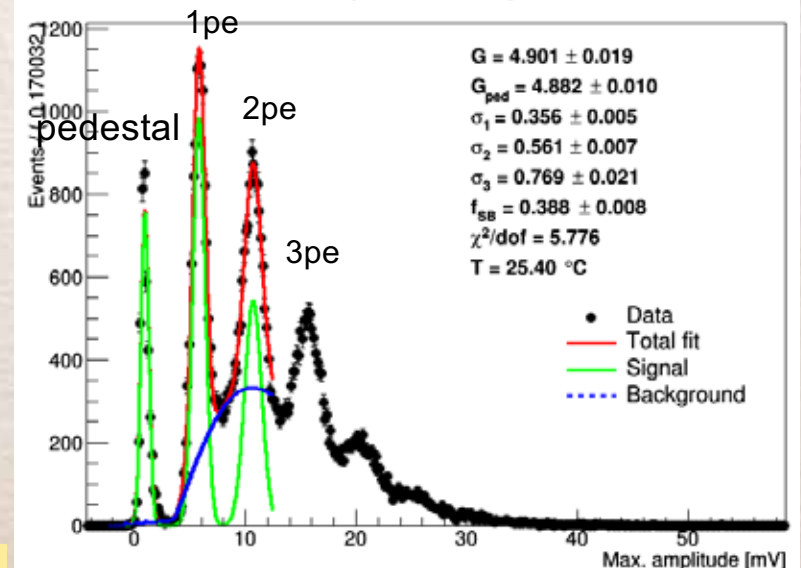
Hamamatsu 12571-10

Spectrum of pe



CPTA #922

Spectrum of pe



Gain Determination

- **Gain:** distance between two adjacent photoelectron peaks
- We choose distance between first and second photoelectron peaks
- Distance between pedestal and first photoelectron peak yields the same gain
- We fit the photoelectron spectra extracted from 50000 waveforms with a likelihood function

$$L = \prod_{i=1}^{50000} \left[f_s F_{sig}(w^i) + (1 - f_s) F_{bkg}(w^i) \right] \quad f_s: \text{signal fraction}$$

- We use two different fit models

$$F_{sig} = f_{ped} G_{ped} + f_1 G_1 + (1 - f_{ped} - f_1) G_2$$

- First model:

separate Gaussian G_i for pedestal, first p.e. & second pe peaks and fractions f_{ped} , f_1 ; include background F_{bkg} determined by a sensitive nonlinear iterative peak-clipping algorithm (SNIP) available in ROOT

- Second model:

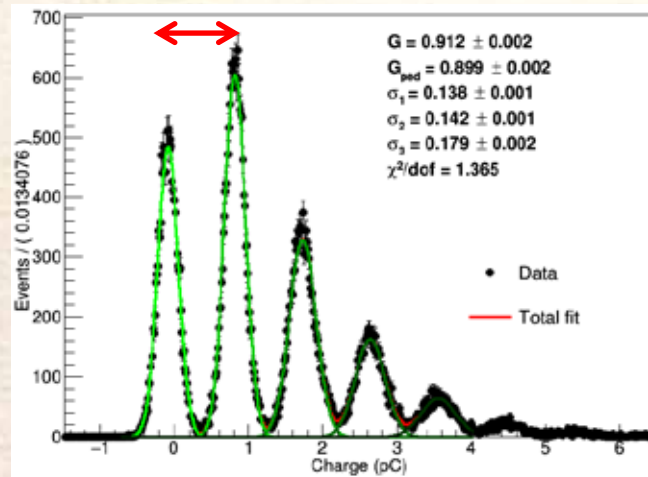
$$F_{sig} = f_{ped} G_{ped} + \sum_{i=1}^{n-1} f_i G_i + \left(1 - f_{ped} - \sum_{i=1}^{n-1} f_i \right) G_n$$

→ fit pedestal and all visible peaks with Gaussians G_{ped} and G_i , where all widths and fit fractions are kept as free parameters, use no background pdf

Two Fit Models

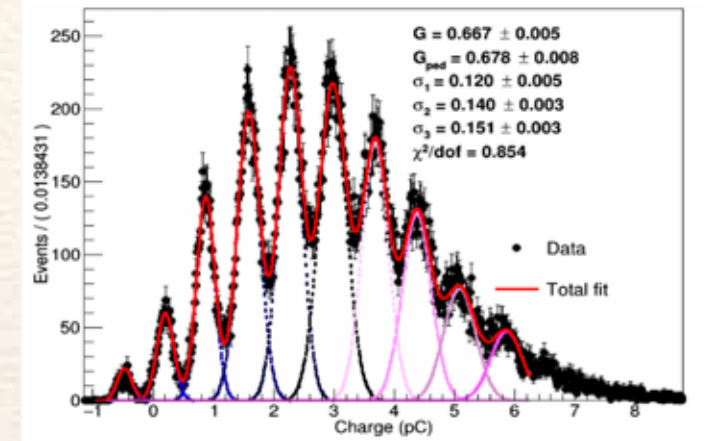
First fit model

Hamamatsu
S12571



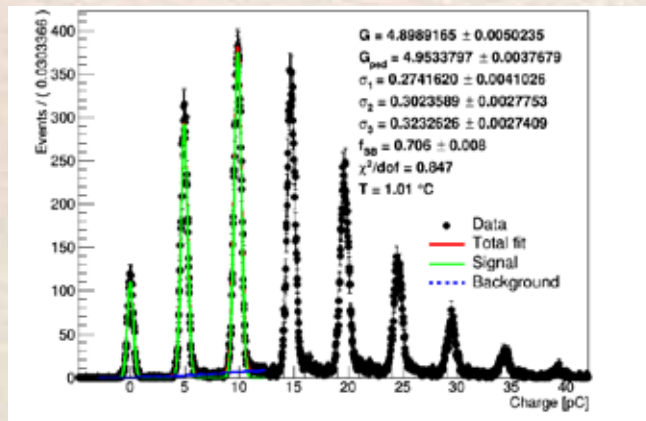
Second fit model

Hamamatsu B1



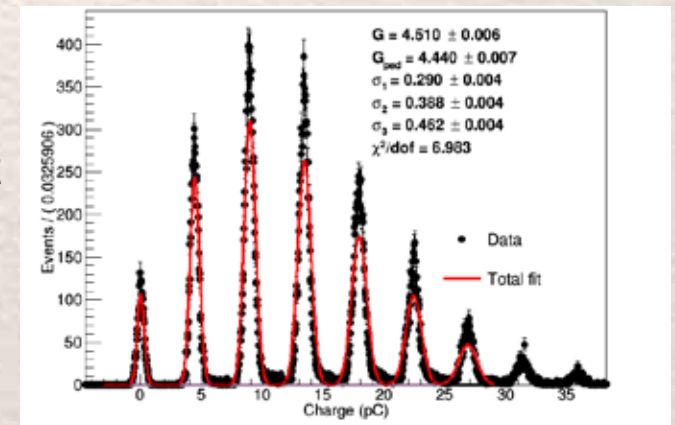
Use first fit model for bias voltage scans of all SiPMs and gain stability tests of Hamamatsu MPPCs with trenches

Hamamatsu
S13360 with
fit model 1



Second fit model yields poor fits without modeling of tails on right-hand side

Hamamatsu S13360 with fit model 2

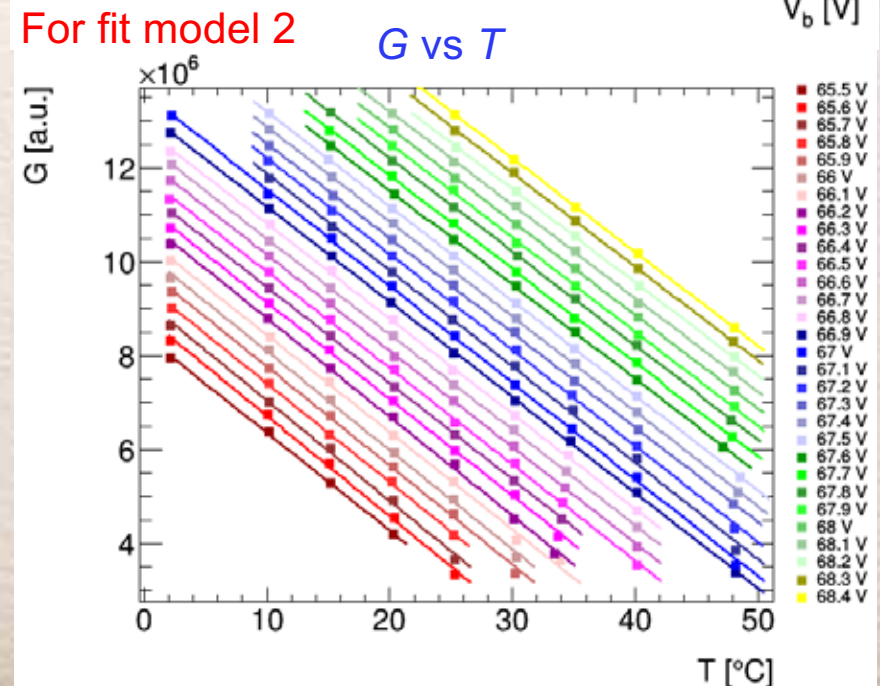
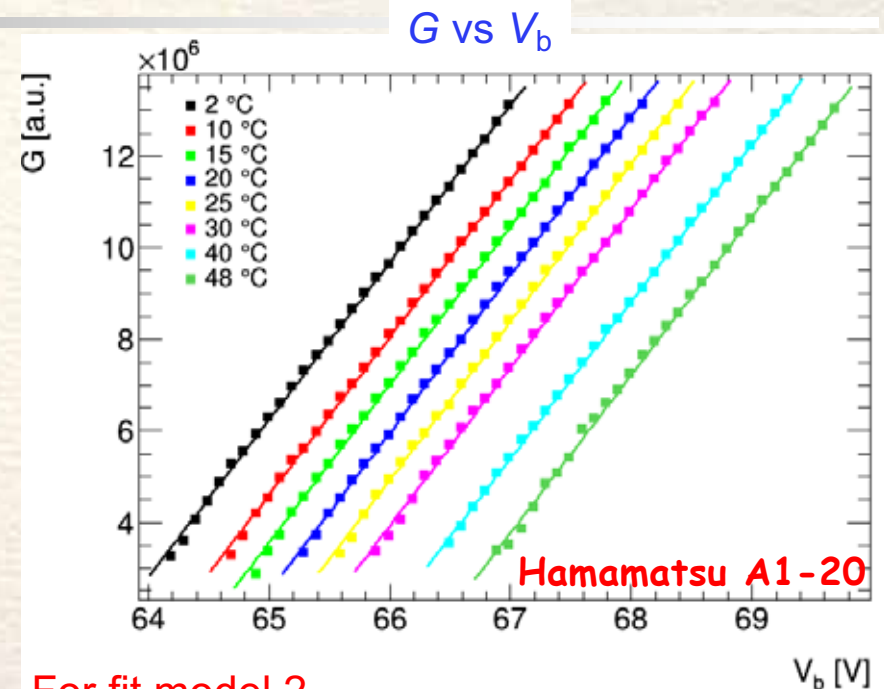
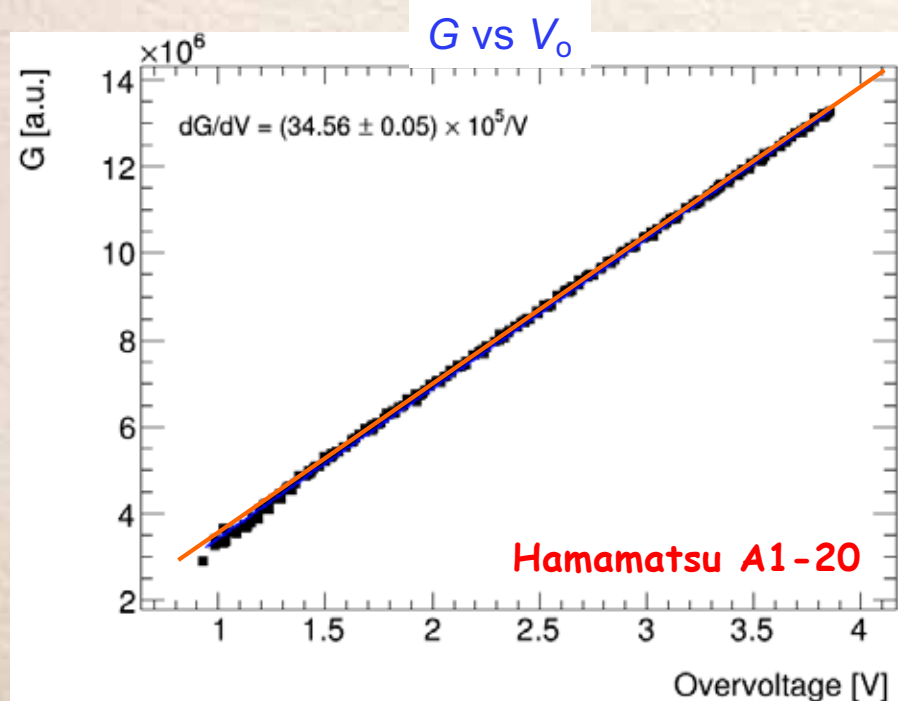


Use second fit model for gain stability tests of all Hamamatsu MPPCs without trenches, all KETEK and CPTA SiPMs, for bias voltage scans of some MPPCs without trenches



Measurement of G versus V_b and T

- We explore the 2°C-48°C temperature range
- At different fixed T , we measure G vs V_b
→ at each point we take 50k waveforms
- The dependences G vs V_b for each T and G vs T for each V_b are linear with similar slopes
- Plotting G vs overvoltage V_o shows that for $V_o > 1.5$ V all gains show a linear dependence on V_o independent of T

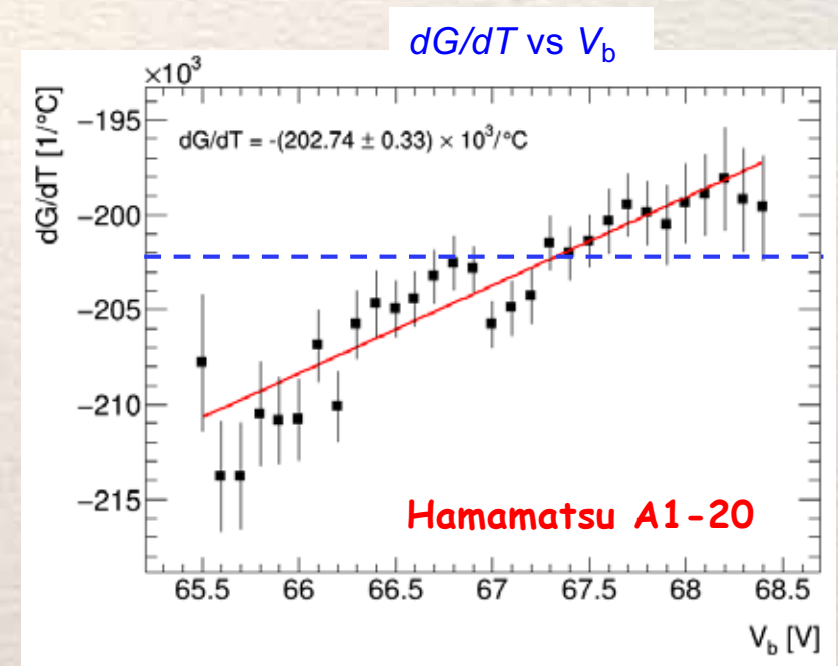
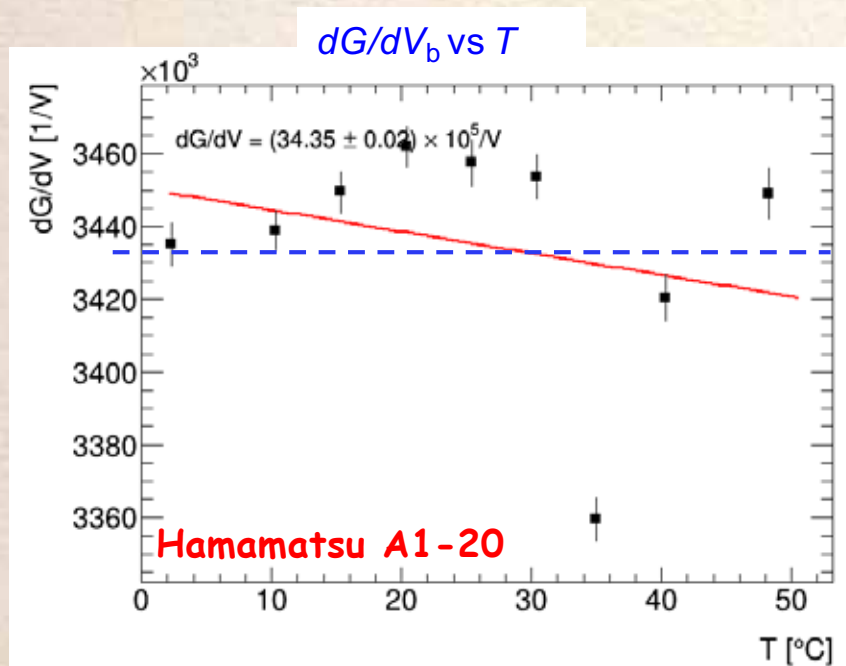


Determination of dG/dV_b and dG/dT

- We perform a simultaneous fit of G versus V_b and T to extract dG/dV_b and dG/dT

$$G = G(V_0, T_0) + \frac{dG(V_b, T)}{dV_b} ((V - V_0)) + \frac{dG(V, T)}{dT} ((T - T_0))$$

- We use fit model 2; we get consistent results with fit model 1
- We take averages for dG/dV_b and dG/dT ; deviations from uniformity are $< 2\%$



- $dG/dV_b = (34.35 \pm 0.1) \times 10^5/\text{V}$

- $dG/dT = -(2.0274 \pm 0.0033) \times 10^5/^\circ\text{C}$

Determination of dV_b/dT

- We calculate dV_b/dT from dG/dT and dG/dV_b

$$\frac{dV_b}{dT} = \frac{dG(V_b, T)/dT}{dG(V_b, T)/dV_b}$$

- We determine

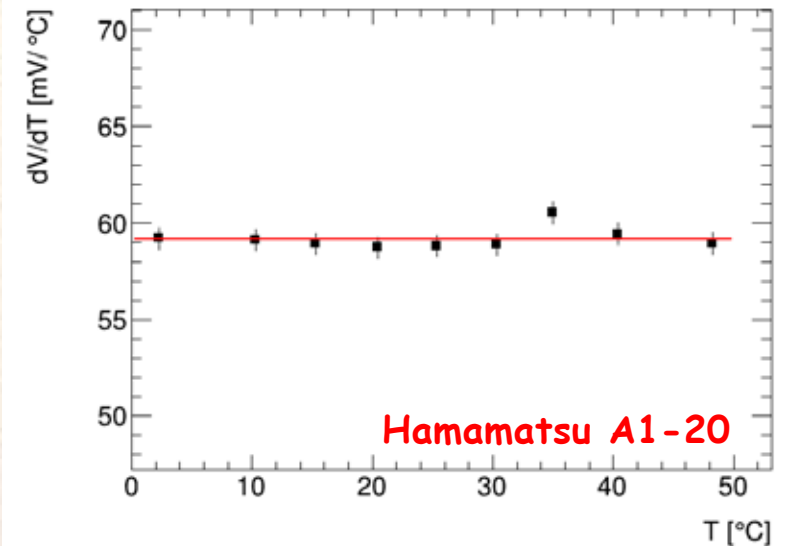
$$dV_b/dT = (59.1 \pm 0.1) \text{ mV/}^\circ\text{C}$$

- The error includes the covariance of $(dG/dV_b, dG/dT)$
- From the breakdown voltage V_{break} vs T we extract

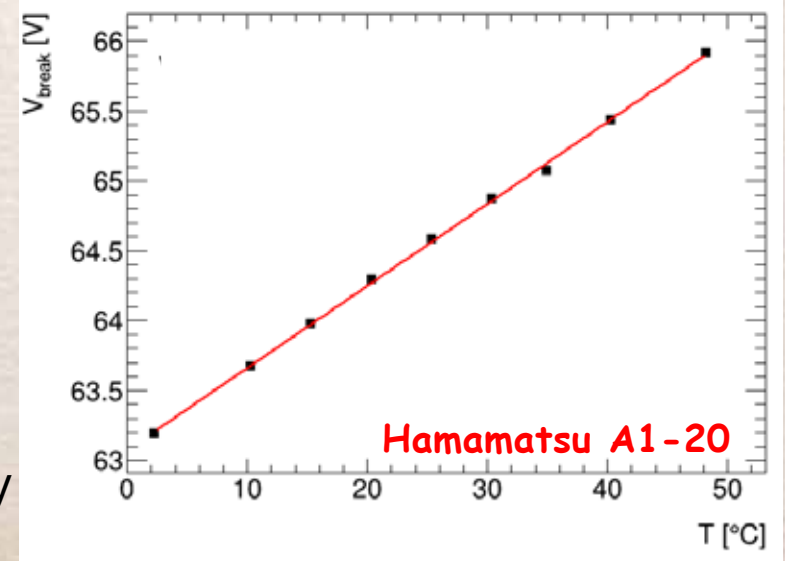
$$dV_b/dT = (58.7 \pm 0.3) \text{ mV/}^\circ\text{C}$$

- For stabilization of Hamamatsu type A MPPCs we used $dV_b/dT = 59.0 \text{ mV/}^\circ\text{C}$
- The breakdown voltage increases linearly with T
 $\rightarrow dV_b/dT$
- The $V(T)$ dependence can be calculated analytically (see backup slides)

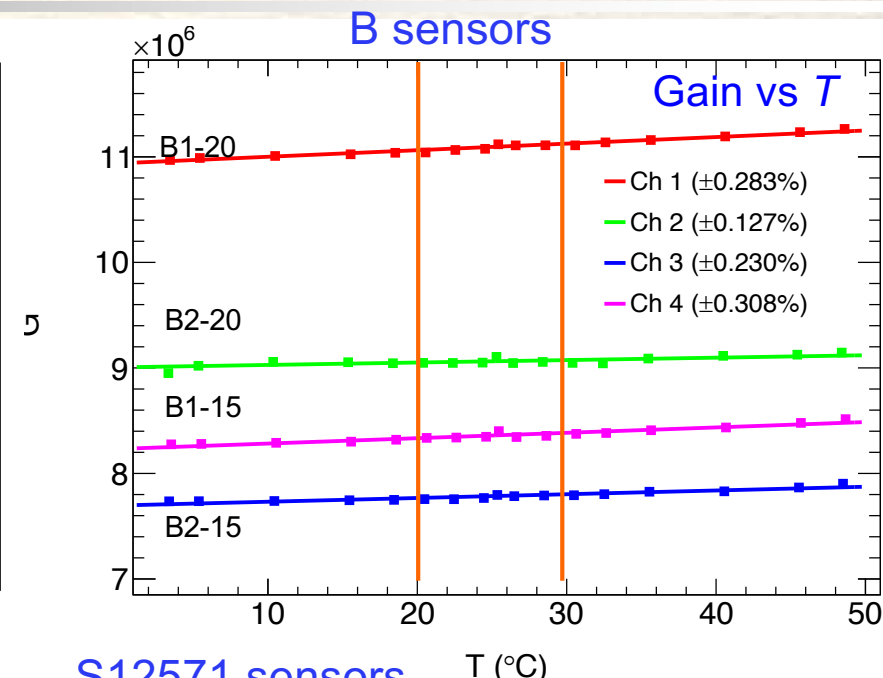
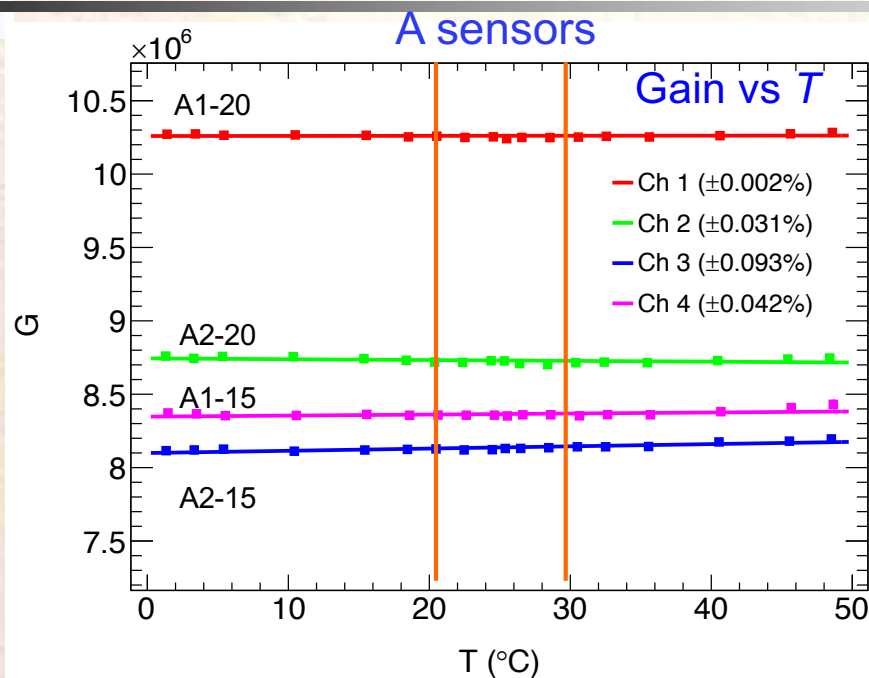
dV_b/dT vs T



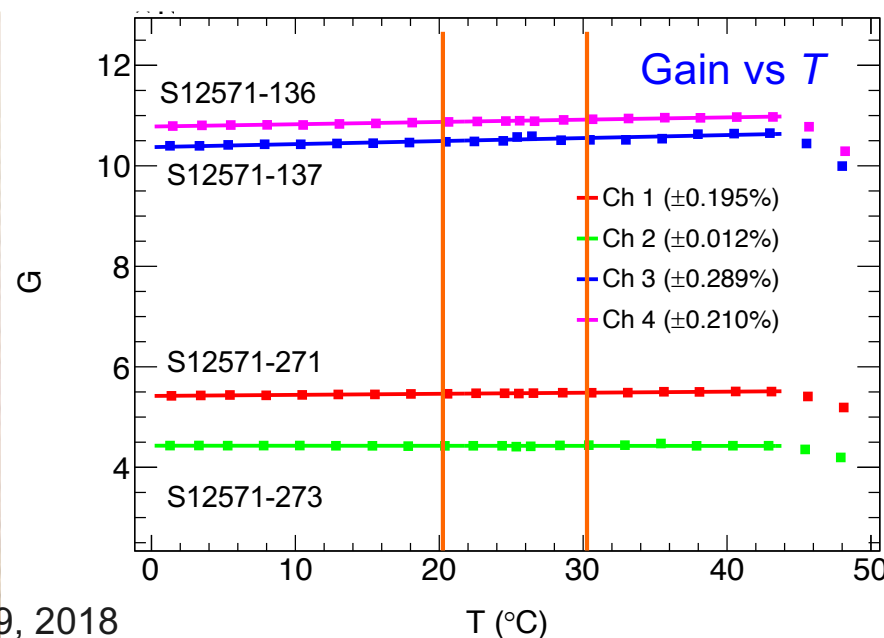
V_{break} vs T



Gain Stabilization: Hamamatsu MPPCs w/o Trenches



S12571 sensors

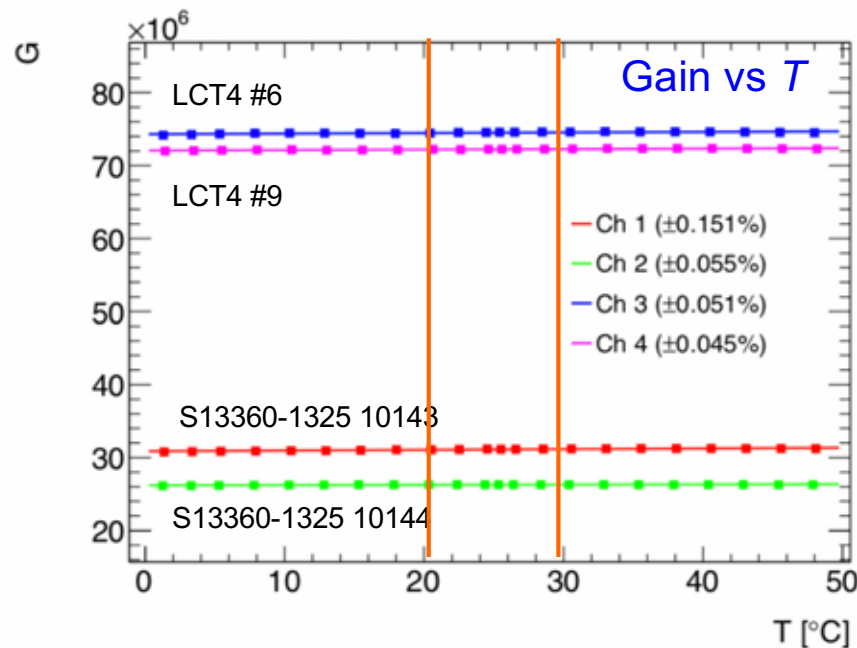


- Fit p.e. spectra of all MPPCs without trenches with **fit model 2**
- All 12 MPPCs satisfy our requirement of $\Delta G/G < \pm 0.5\%$ in $20^{\circ} - 30^{\circ}\text{C}$ T range
- Some MPPCs satisfy this requirement in the entire T range $2^{\circ} - 48^{\circ}\text{C}$

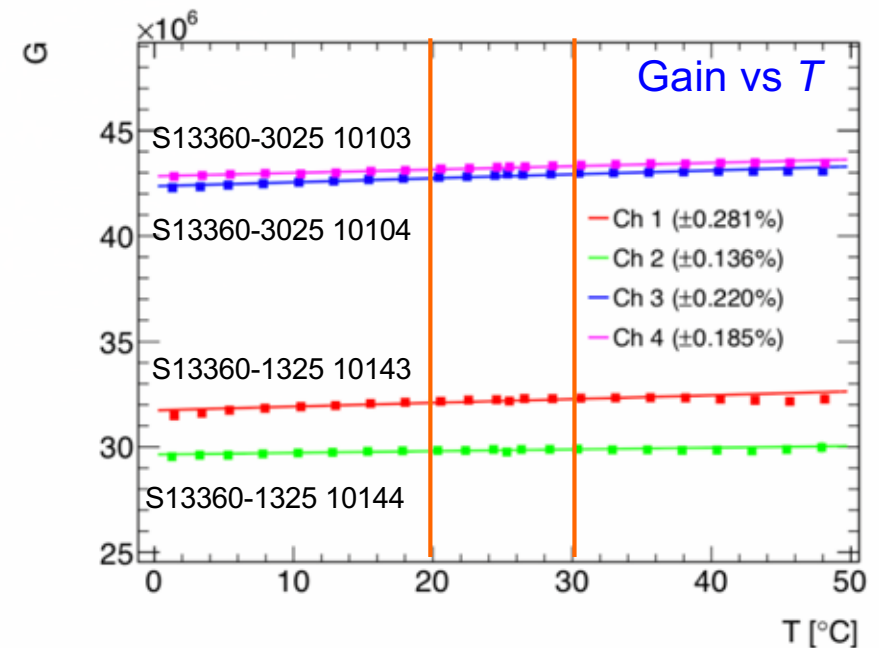


Gain Stabilization: Hamamatsu MPPCs w Trenches

S13360-1325 & LCT4 sensors



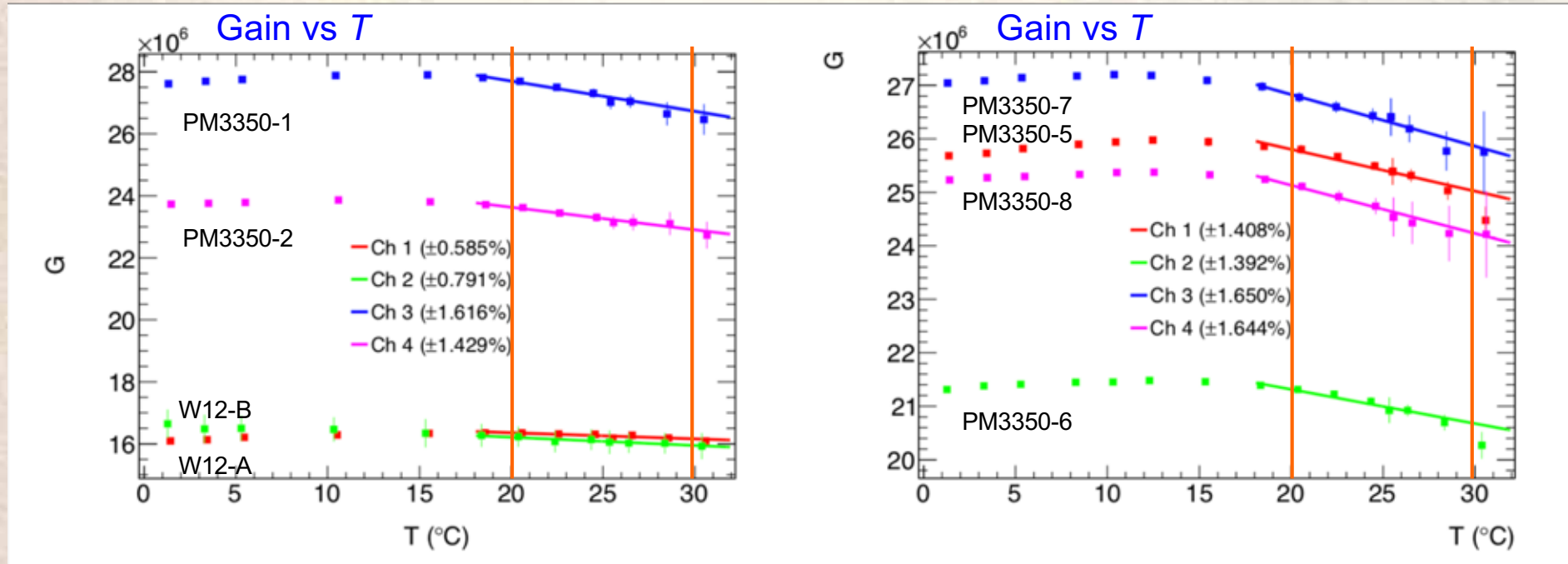
All S13360 sensors



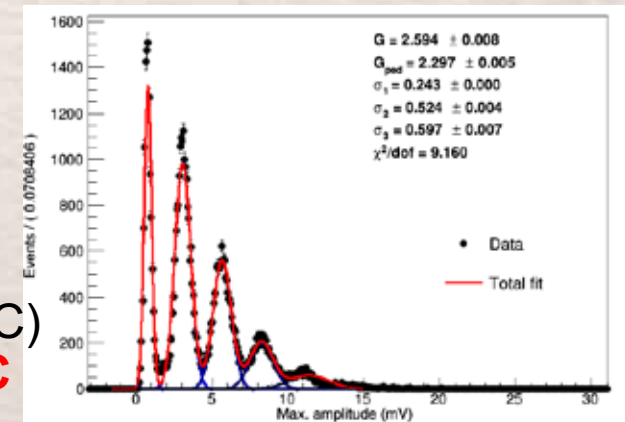
- Fit photoelectron spectra of all MPPCs with trenches with **fit model 1**
- All 6 MPPCs satisfy our requirement of $\Delta G/G < \pm 0.5\%$ in $20^{\circ} - 30^{\circ}\text{C}$ T range
- Both LCT4 and some S13360 sensors satisfy $\Delta G/G < \pm 0.5\%$ in $2^{\circ} - 48^{\circ}\text{C}$ T range

Gain Stabilization of KETEK SiPMs

- Simultaneous gain stabilization for 4 KETEK SiPMs in two batches: $dV_b/dT=18.2 \text{ mV/}^\circ\text{C}$

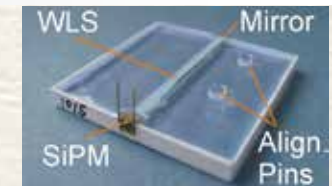


- Fit all photoelectron spectra with fit model 2
- KETEK SiPMs show more complicated $V(T)$ behavior
 - linear correction is not sufficient
 - sensors do not function properly above 30°C
 - G rises ($1-18^\circ\text{C}$); uniform G ($18-22^\circ\text{C}$); G falls off ($22-30^\circ\text{C}$)
 - due to this complicated $V(T)$ behavior, $dV_b/dT \sim 21 \text{ mV/}^\circ\text{C}$

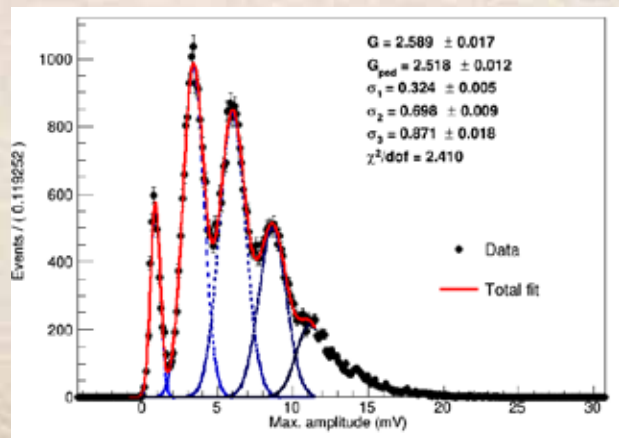


Thus, no SiPM satisfies the $< \pm 0.5\%$ requirement for $T=20^\circ - 30^\circ\text{C}$ range

Gain Stabilization of CPTA SiPMs

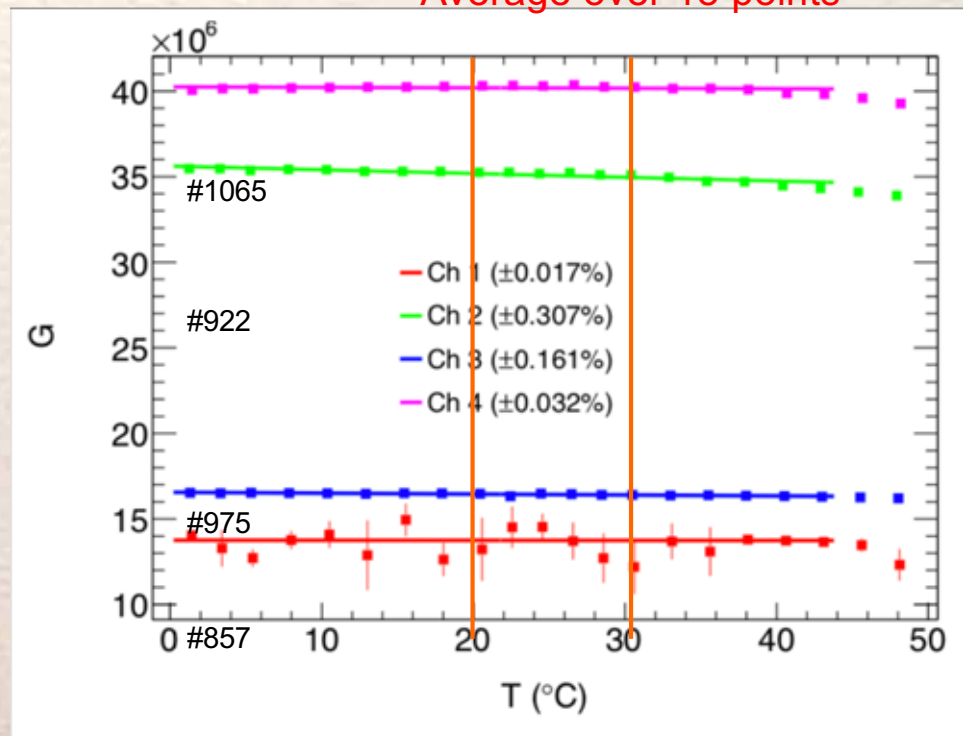


- CPTA SiPMs are illuminated via scintillator tile
- We adjust V_b with regulator board using $dV_b/dT=21.2 \text{ mV}/^\circ\text{C}$ to stabilize 4 CPTA SiPMs simultaneously
- We test gain stability within $T=2^\circ - 48^\circ\text{C}$ taking ≥ 18 samples of 50k waveform samples at each T
- The gain is nearly uniform up to 30°C
- SiPMs in ch#2 and ch#4 look fine; ch#1 is noisy, ch#3 changed gain at $T=45^\circ\text{C}$ but looks ok
- All 4 SiPMs satisfy our requirement of $>\pm 0.5\%$ within $20^\circ\text{C} - 30^\circ\text{C}$ T range



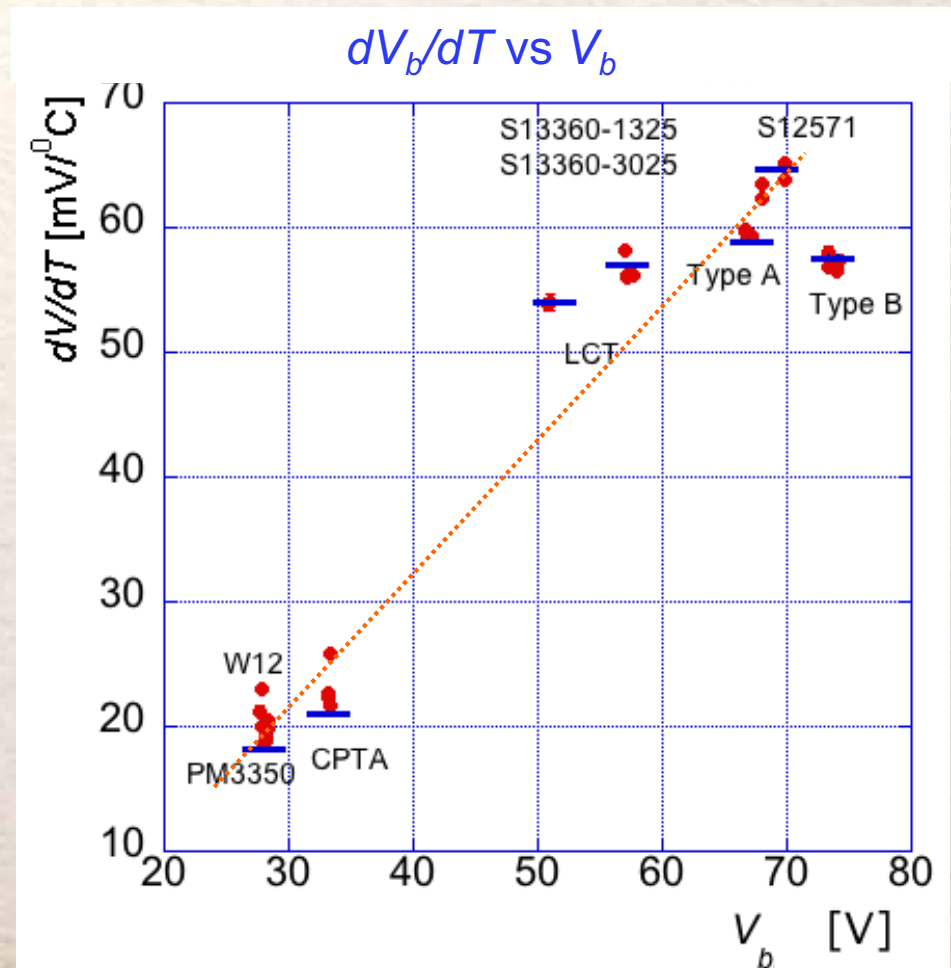
Gain vs T

Average over 18 points



Measured dV_b/dT Values versus V_b

- Look for correlations between operating voltage and measured dV_b/dT for all SiPMs
- For most SiPMs dV_b/dT increases linearly with V_b
- Exceptions:
 - Hamamatsu B type MPPCs
 - Hamamatsu MPPCs with trenches
 - They have lower V_b for similar dV_b/dT
- KETEK & CPTA SiPMs have larger dV_b/dT spread than Hamamatsu MPPCs without trenches



Does Afterpulsing affect Gain Stabilization?

- We determine the pe spectra from the waveforms in 2 ways

- integrated charge Q
- magnitude of the peak A_{peak}

- We analyze the scatter plot of Q versus A_{peak}

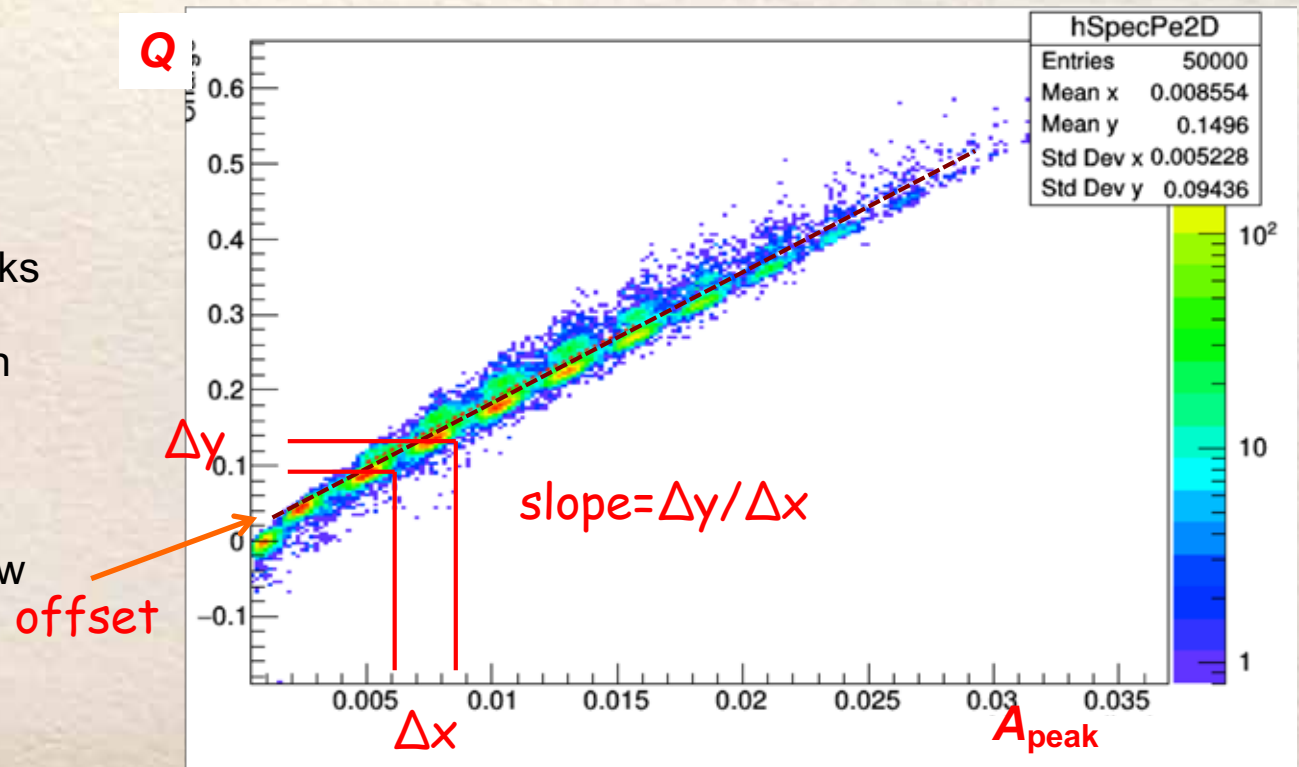
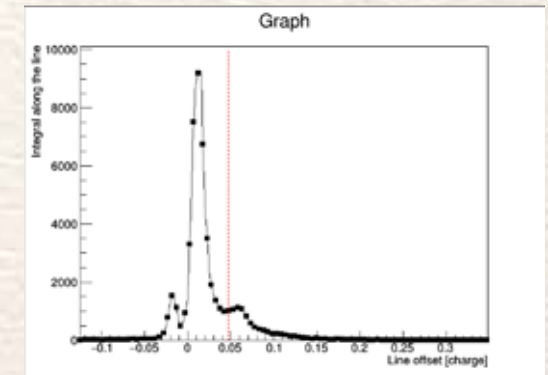
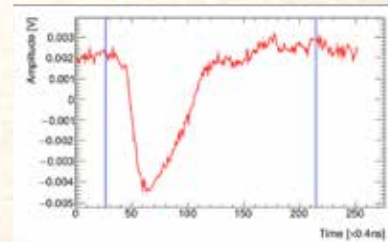
- Signal without afterpulsing lies on the diagonal

- Signal with afterpulsing is shifted upwards since waveform is broadened due to delayed secondary signal

- Set slope with 2pe & 3pe peaks

- Dashed line is chosen to be in valley between the 2 regions
→ best separation

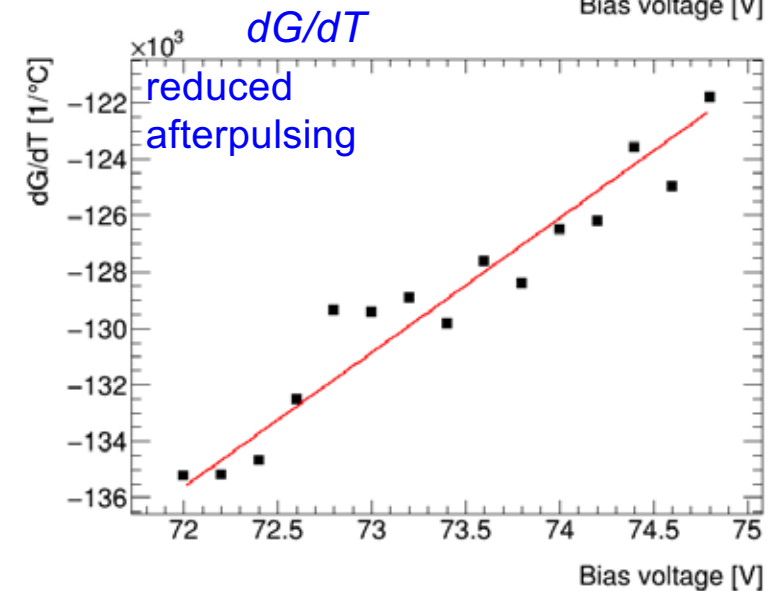
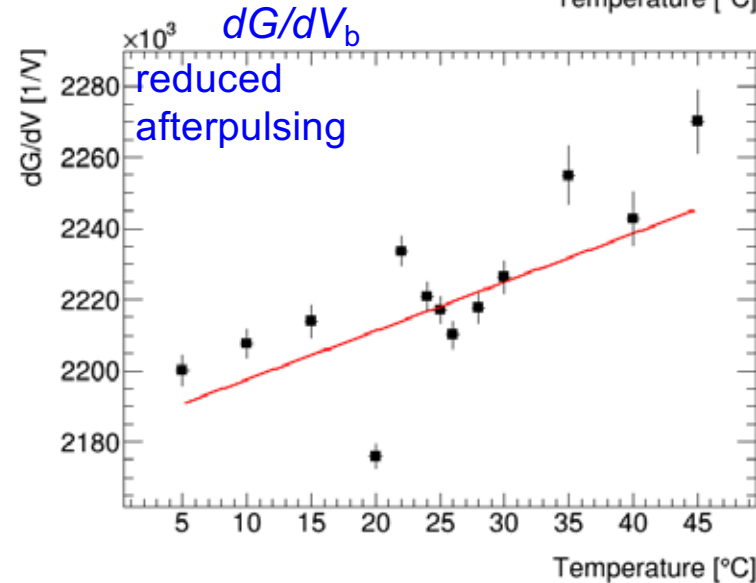
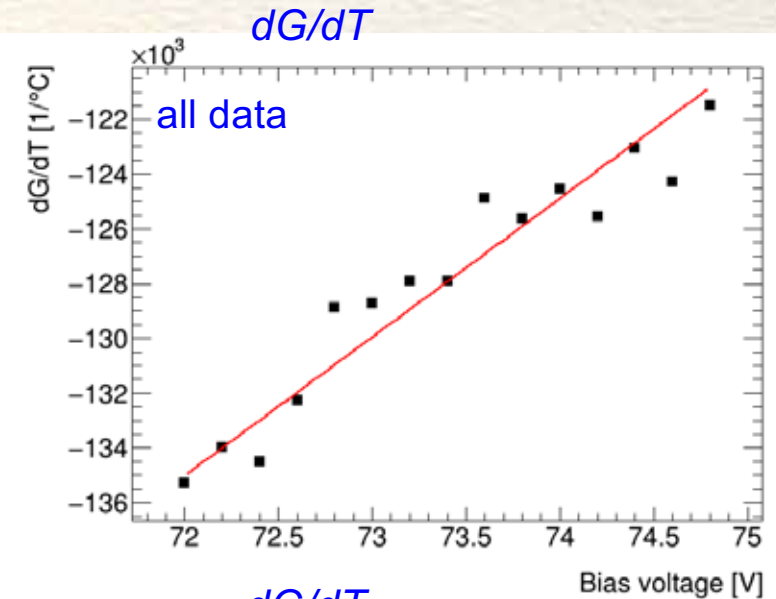
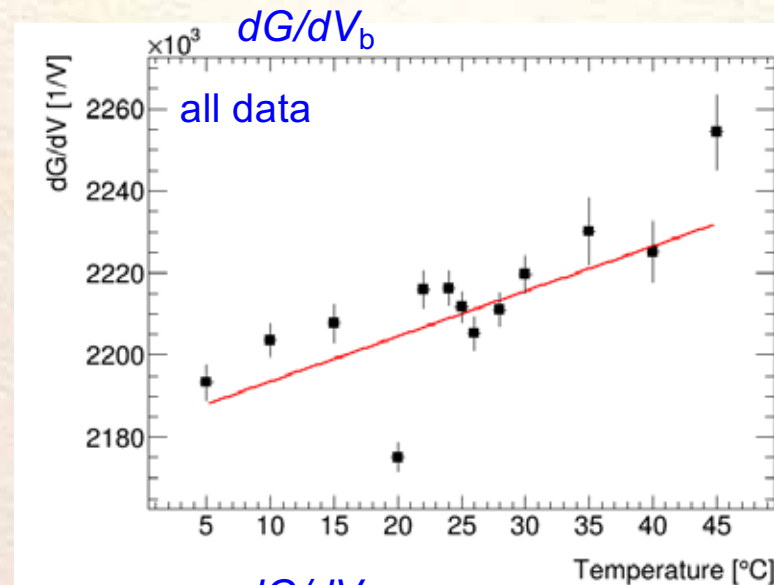
- Redo analysis for region below dashed line



dG/dV_b and dG/dT for Reduced Afterpulsing

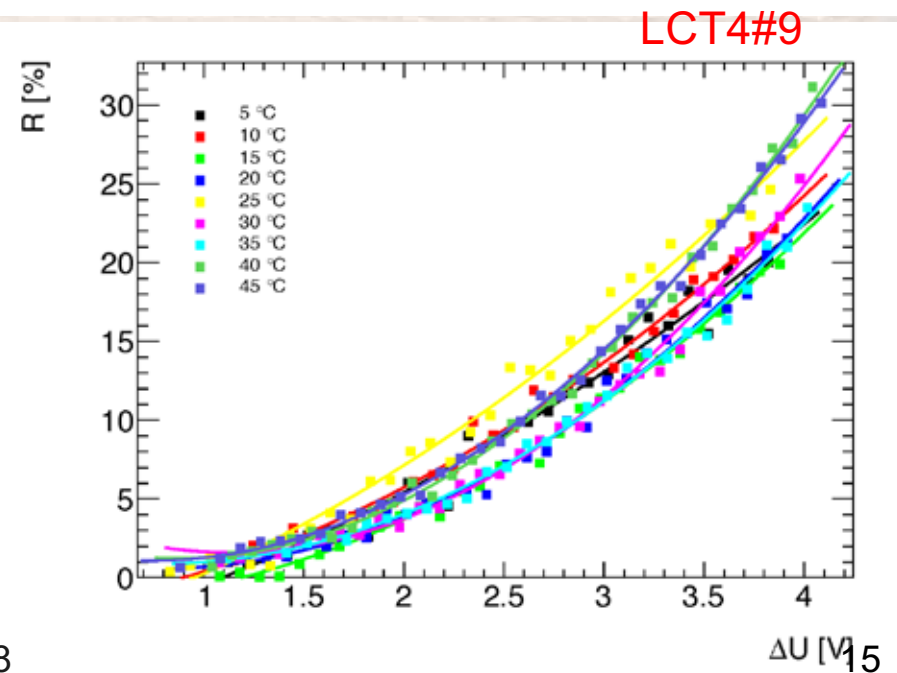
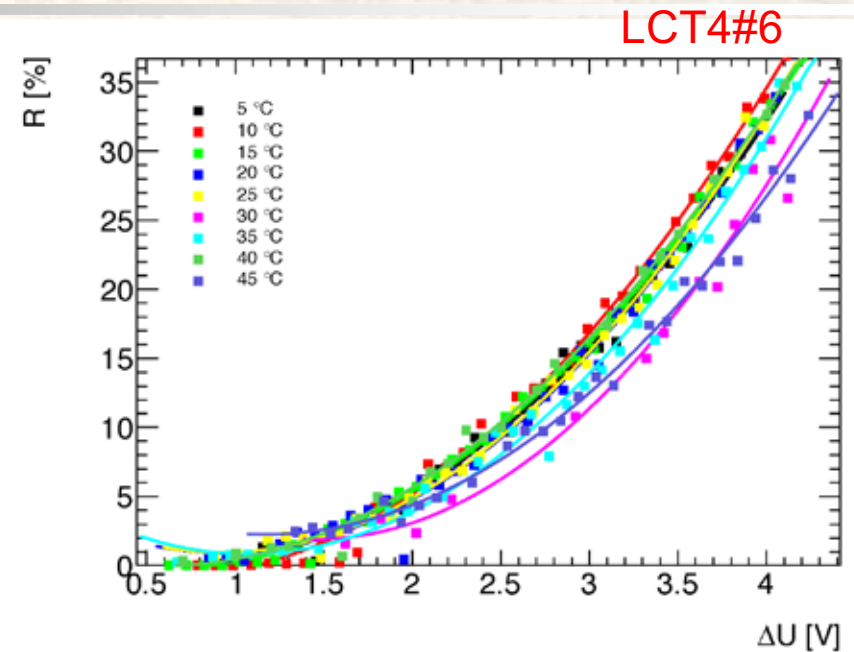
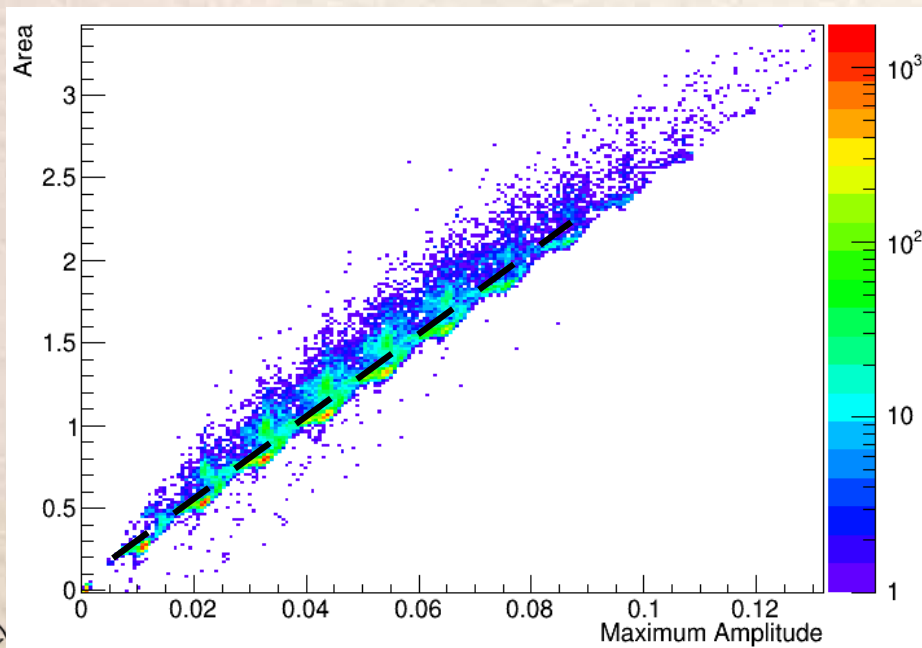
- The dG/dV_b & dG/dT distributions for sample with reduced afterpulsing look similar as those for all data

- Within errors get the same fit results
→ visually slopes of red lines are the same



Afterpulsing of LCT4 MPPCs

- Define afterpulsing
 R =events above dashed line/all events
- Study R as a function of V_b for each T
- R shows rapid increase with V_b
- R shows no explicit T dependence ($T > 0^\circ\text{C}$)
→ Spread may indicate systematic effects of procedure





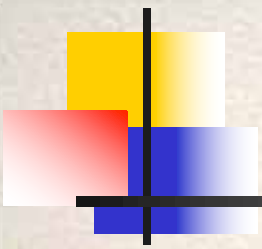
Conclusion and Outlook

- We successfully completed gain stabilization tests for 30 SiPMs and demonstrated that batches of similar SiPMs can be stabilized with **one** dV_b/dT compensation value
- All 18 Hamamatsu MPPCs satisfy the stabilization goal: $\Delta G/G < \pm 0.5\%$ for $T=20^\circ\text{C}-30^\circ\text{C}$
→ most MPPCs satisfy $\Delta G/G < \pm 0.5\%$ in the extended T range $2^\circ\text{C}-48^\circ\text{C}$
- Gain stabilization of KETEK SiPMs is more complicated
 - Range of stabilization is limited to $2^\circ\text{C}-30^\circ\text{C}$ T range
 - No SiPM satisfies our requirement → need individual dV_b/dT values
- Gain stabilization of CPTA SiPMs works fine
→ for all 4 SiPMs, $\Delta G/G < \pm 0.5\%$ is satisfied in $20^\circ\text{C}-30^\circ\text{C}$ range
- Afterpulsing does not affect gain stabilization results
- Afterpulsing strongly depends on overvoltage not temperature ($T > 0^\circ\text{C}$)
- Results are in the process of publication in JINST
- In the analog HCAL, V_b adjustment can be implemented on the electronics board
→ need array of temperature sensors to monitor T adequately in entire AHCAL



Acknowledgments

- We would like to thank L. Linssen, Ch. Joram, W. Klempt, and D. Dannheim for using the E-lab and for supplying electronic equipment
- We thank Yamamoto-san for providing A, B and LCT4 sensors
- We further would like to thank the team of the climate chamber at CERN for their support

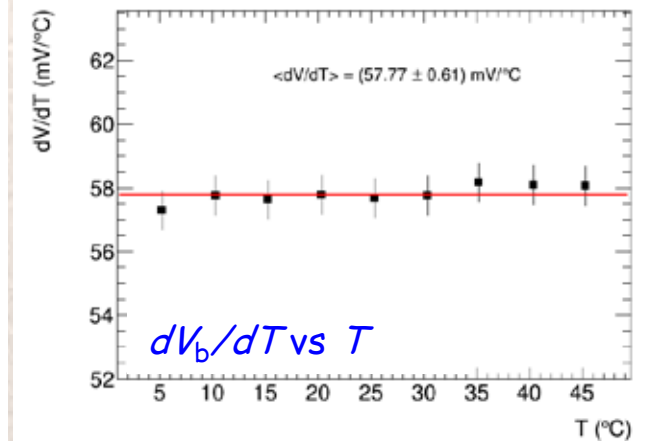
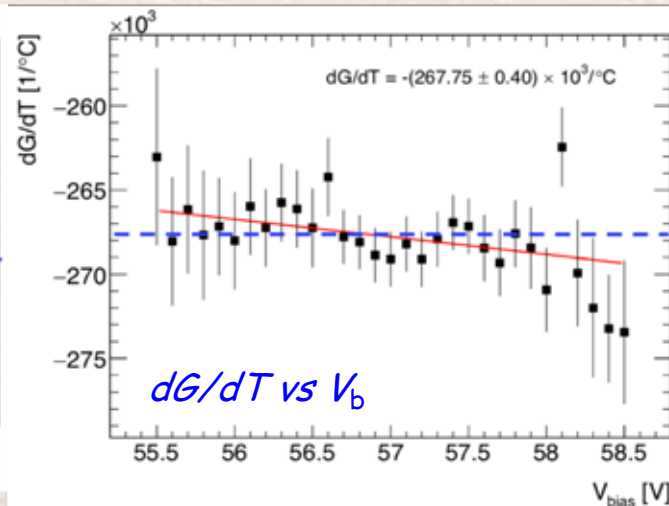
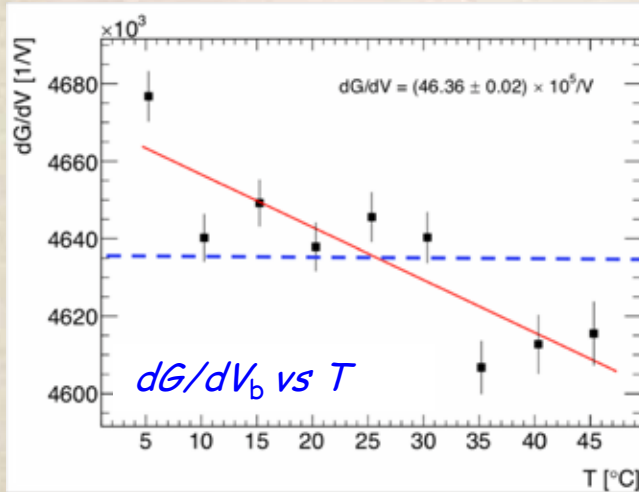
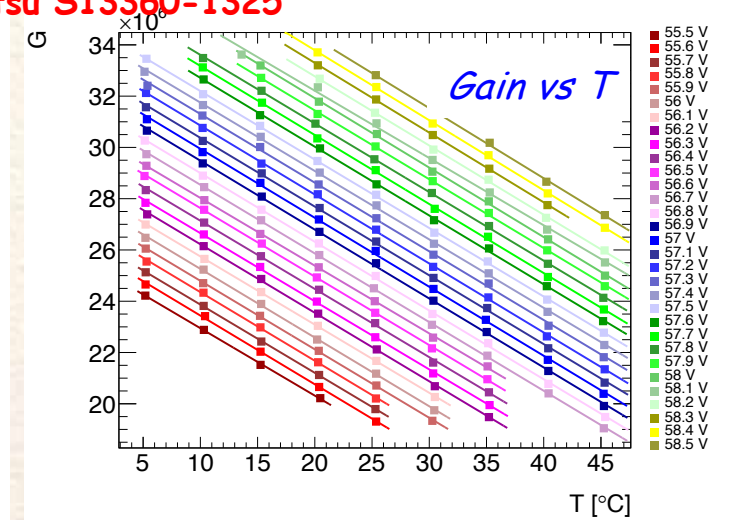
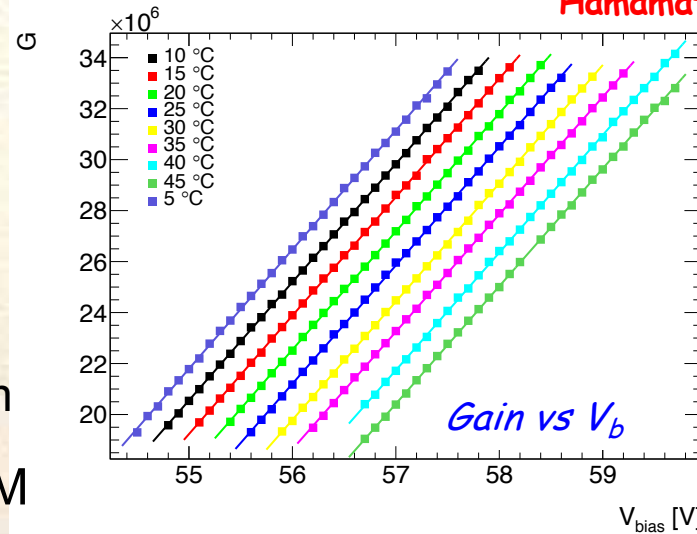


Backup Slides

dG/dV_b , dG/dT & dV_b/dT Results for Fit Model 1

- For fixed T , measure G vs $V_b \rightarrow dG/dV_b$
- For fixed V_b plot G vs $T \rightarrow dG/dT$
- Extract all dV_b/dT for fixed T & average them
- Do this for each SiPM
- Fit dG/dV_b and dG/dT with linear functions, use only constant (slope are small <1%)

Hamamatsu S13360-1325



$dG/dV = (46.36 \pm 0.02_{\text{stat}}) \times 10^5/V$

$dG/dT = (2.6775 \pm 0.004) \times 10^5/^\circ\text{C}$

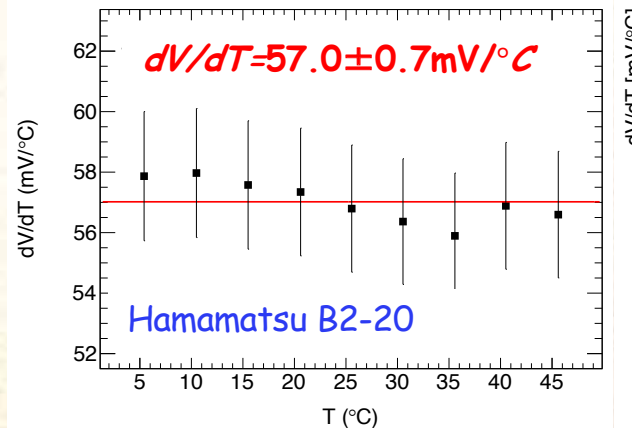
$dV_b/dT = (57.8 \pm 0.1_{\text{sys}}) \text{ mV}/^\circ\text{C}$



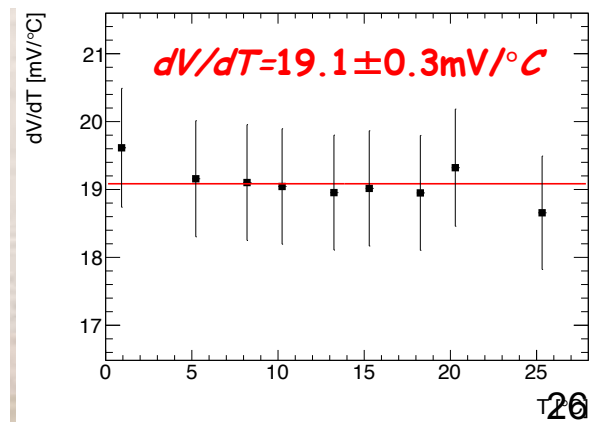
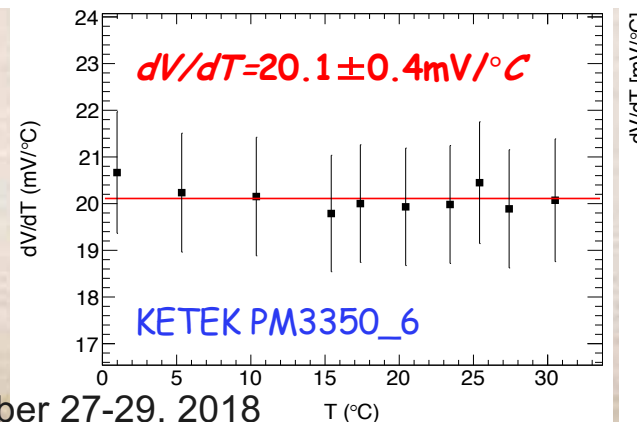
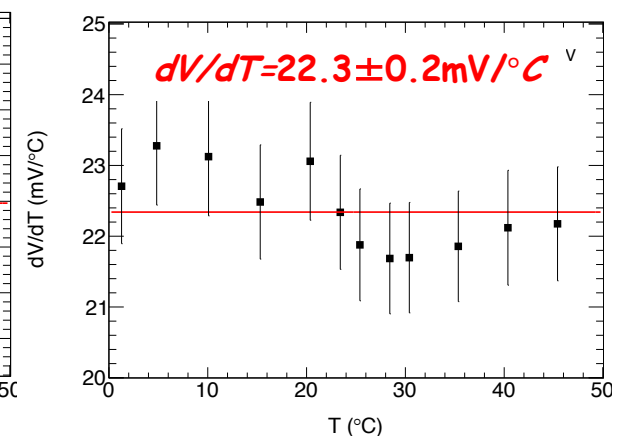
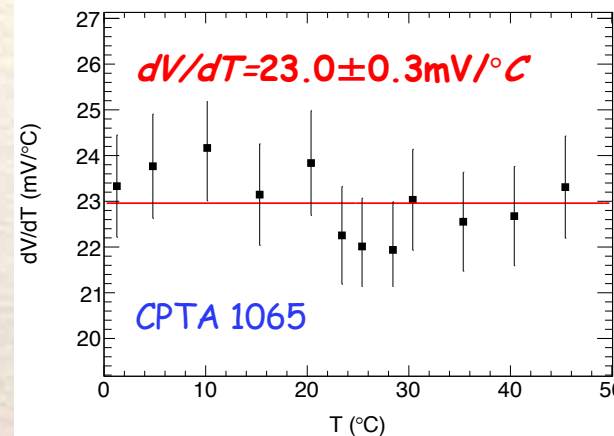
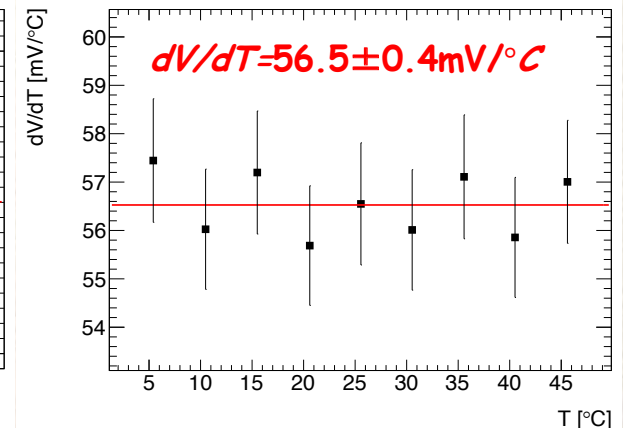
Comparision of the 2 Fitting Strategies

- We obtain the **same** dV/dT for Hamamatsu A, B & S12571 MPPCs within errors for both fitting strategies
- For KETEK and CPTA SiPMs we have tested the new fitting methodology on one channel so far
- For these two SiPMs, dV/dT values agree within two agree within 2 standard deviations
- We will do the remaining KETEK and CPTA SiPMs soon

New fit



Old fit



SiPM Properties

● Test 18 Hamamatsu MPPCs (6 w trenches), 8 KETEK SiPMs and 4 CPTA SiPMs

SiPM	Serial#	Size [mm ²]	Pitch [μm]	#pixels	V _{bias} [V]	Gain [10 ⁶]	SiPM	Serial#	Size [mm ²]	Pitch [μm]	#pixels	V _{bias} [V]	Gain [10 ⁶]
Type A	A1	1×1	15	4440	67.22	0.2	W12	1	3×3	20	12100	28	0.54
Type A	A2	1×1	15	4440	67.15	0.2	W12	2	3×3	20	12100	28	0.54
Type A	A1	1×1	20	2500	66.73	0.23	PM33	1	3×3	50	3600	28	8
Type A	A2	1×1	20	2500	67.7	0.23	PM33	2	3×3	50	3600	28	8
Type B	B1	1×1	15	4440	74.16	0.2	PM33	5	3×3	50	3600	28	8
Type B	B2	1×1	15	4440	73.99	0.2	PM33	6	3×3	50	3600	28	8
Type B	B1	1×1	20	2500	73.33	0.23	PM33	7	3×3	50	3600	28	8
Type B	B2	1×1	20	2500	73.39	0.23	PM33	8	3×3	50	3600	28	8
S12571	271	1×1	10	10000	69.83	1.35	CPTA	857	1×1	40	625	33.4	0.71
S12571	273	1×1	10	10000	69.87	1.35	CPTA	922	1×1	40	625	33.1	0.63
S12571	136	1×1	15	4440	68.08	2.29	CPTA	975	1×1	40	625	33.3	0.63
S12571	137	1×1	15	4440	68.03	2.30	CPTA	1065	1×1	40	625	33.1	0.70
LCT4	6	1×1	50	400	53.81	1.6							
LCT4	9	1×1	50	400	53.98	1.6							
S13360	10143	1.3×1.3	25	2668	57.18	0.7							
S13360	10144	1.3×1.3	25	2668	57.11	0.7							
S13360	10103	3×3	25	14400	57.6	1.7							
S13360	10104	3×3	25	14400	56.97	1.7							

- Use 3 types of MPPCs with trenches
- Two experimental samples (LCT4)
 - Two 1.3 × 1.3 mm² sensors
 - Two 3 × 3 mm² sensors

Exact dV_b/dT Relation

- For stable gain, extract \rightarrow

$$\frac{dV}{dT} = - \frac{\left(\partial G(V,T) / \partial T \right)}{\left(\partial G(V,T) / \partial V \right)} V(T)$$

- We observed linear dependence

$$\frac{\partial G(V,T)}{\partial T} = a + bT \quad \text{and}$$

$$\frac{\partial G(V,T)}{\partial V} = c + dV$$

- The analytic solution is

$$V(T) = -\frac{a}{b} + \frac{K}{(c + dT)^{b/d}} \quad \text{K: integration constant}$$

for $b \neq 0, d \neq 0$

- By plugging the values for a, b, c, d for Hamamatsu B2 yields $V(T)$ dependence \rightarrow in the 2°C - 50°C range this yields an excellent linear approximation

$$a = (-0.48266 \pm 0.0002) \times 10^6; \quad b = 4835.9 \pm 0.3; \quad c = (2.17 \pm 0.003) \times 10^6; \quad d = 1295 \pm 152$$

